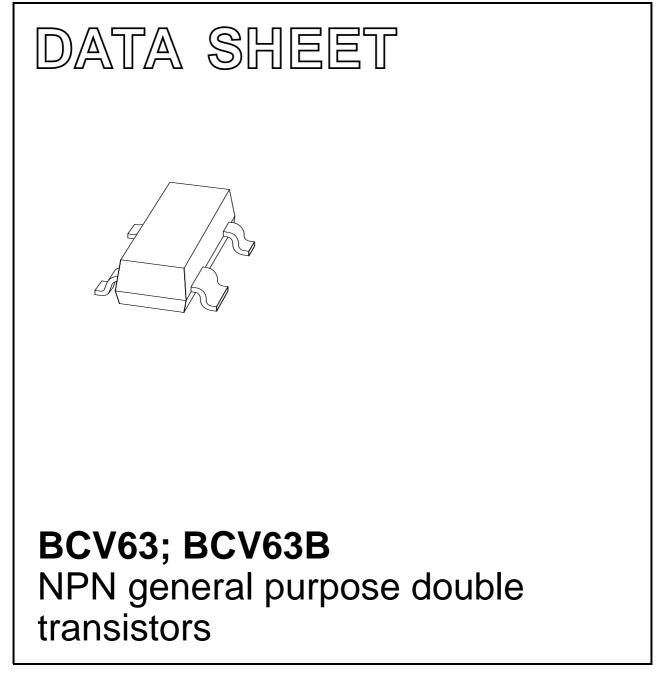
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1997 Mar 10 1999 May 21



BCV63; BCV63B

DESCRIPTION

TR1

MAM316

Fig.1 Simplified outline (SOT143B) and symbol.

TR2

collector TR2 and base TR1

collector TR1

3

base TR2

emitter TR1 and TR2

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 30 and 6 V).

APPLICATIONS

- General purpose switching and amplification
- For use in Schmitt-trigger applications.

DESCRIPTION

NPN double transistor in a SOT143B plastic package. PNP complement: BCV64B.

MARKING

TYPE NUMBER	MARKING CODE
BCV63	D95
BCV63B	D96

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
V _{CBO}	collector-base voltage	open emitter				
	TR1		_	30	V	
	TR2		_	6	V	
V _{CEO}	collector-emitter voltage	open base				
	TR1		_	30	V	
	TR2		_	6	V	
V _{EBO}	emitter-base voltage	open collector	_	6	V	
I _C	collector current (DC)		-	100	mA	
I _{CM}	peak collector current		-	200	mA	
I _B	base current (DC)		_	100	mA	
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1	-	250	mW	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		-	150	°C	
T _{amb}	operating ambient temperature		-65	+150	°C	

PINNING

PIN

1

2

3

4

Top view

Note

1. Transistor mounted on a printed-circuit board.

BCV63; BCV63B

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W	

Note

1. Transistor mounted on a printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	-	-	15	nA
		$I_E = 0; V_{CB} = 30 \text{ V}; T_j = 150 \text{ °C}$	-	-	5	μA
h _{FE}	DC current gain					
	BCV63 TR1	$I_{C} = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	110	-	800	
	BCV63 TR2	I _C = 2 mA; V _{CE} = 700 mV; note 1	110	-	800	
	BCV63B TR1	$I_{C} = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	200	-	450	
	BCV63B TR2	I _C = 2 mA; V _{CE} = 700 mV; note 1	200	-	450	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	_	75	300	mV
	collector-emitter saturation voltage	I _C = 100 mA; I _B = 5 mA				
	TR1		-	250	650	mV
	TR2		_	250	-	mV
V _{BEsat}	base-emitter saturation voltage	$I_{C} = 10 \text{ mA}; I_{B} = 0.5 \text{ mA}; \text{ note } 2$	_	700	-	mV
	base-emitter saturation voltage	I _C = 100 mA; I _B = 5 mA; note 2				
	TR1		_	-850	-	mV
V_{BE}	base-emitter voltage					
	TR1	I _C = 2 mA; V _{CE} = 5 V; note 3	600	650	750	mV
	TR1	$I_{C} = 10 \text{ mA}; V_{CE} = 5 \text{ V}; \text{ note } 3$	-	-	820	mV
	TR2	$I_{C} = 2 \text{ mA}; V_{CE} = 700 \text{ mV}; \text{ note } 3$	_	700	-	mV
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz				
	TR1		-	4	-	pF
f _T	transition frequency	$I_{C} = 10 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$				
	TR1		100	-	-	MHz

Notes

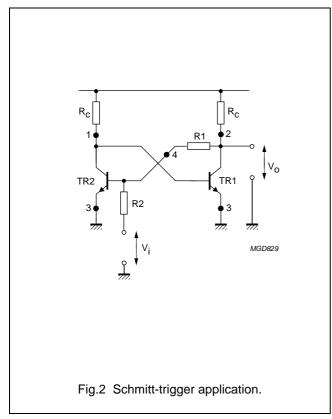
1. Group selection will be done on TR1. Due to matched dies, h_{FE} values for TR2 are the same as for TR1.

2. V_{BEsat} decreases by approximately 1.7 mV/K with increasing temperature.

3. V_{BE} decreases by approximately 2 mV/K with increasing temperature.

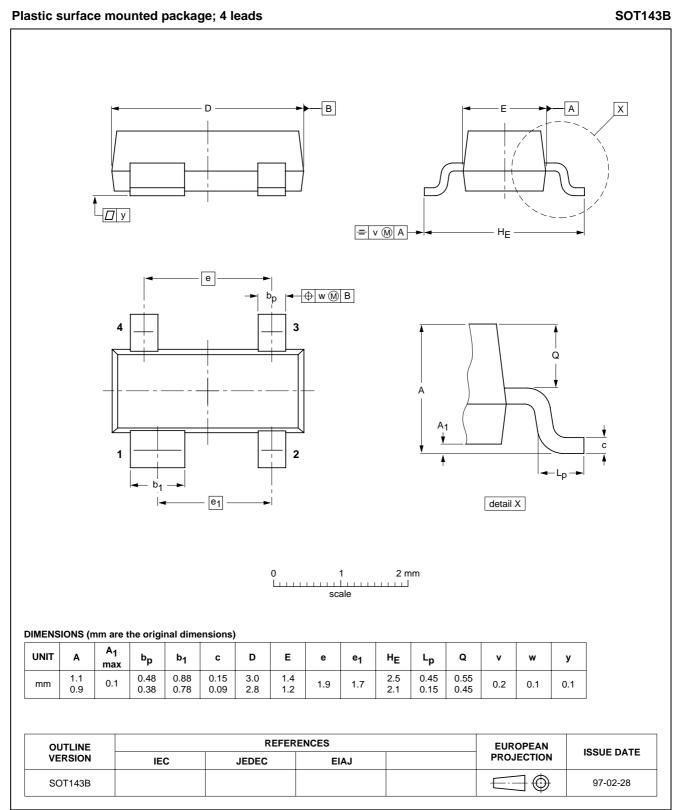
BCV63; BCV63B

APPLICATION INFORMATION



BCV63; BCV63B

PACKAGE OUTLINE



BCV63; BCV63B

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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